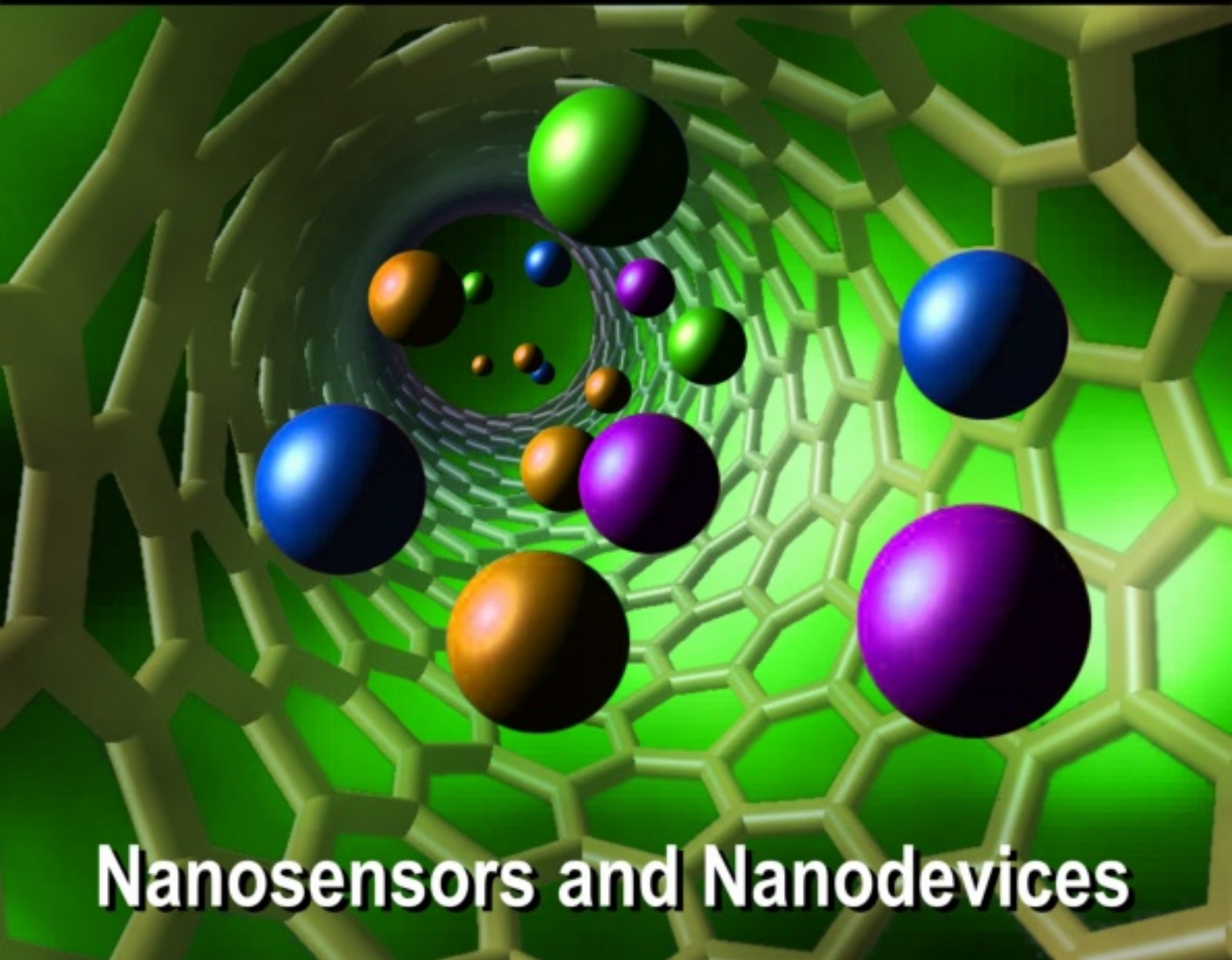


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Trace Moisture Response Property of Thin Film Nano Porous γ -Al₂O₃ for Industrial Application

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Abstract: Nano porous thin film γ -Al₂O₃ is prepared by sol-gel method by heat treating process at 550⁰C. The samples are made of various coating thickness and investigated as trace moisture sensor at room temperature within the range of -72⁰C to -42⁰C dew point (DP). It is found that at a particular coating thickness the sensitivity and response time are found to be suitable for commercial application. The capacitance change over the dew point (DP) range from -72⁰C to -42⁰C is found to be prominent for making a sensitive device. *Copyright © 2007 IFSA.*

Keywords: Thin film, Nanopore, γ -Al₂O₃, Coating thickness, Suitable for making device

1. Introduction

Thin film technology is found to be in many applications [1-9], including microelectronics, optics, magnetic, hard and corrosion resistant coating, micro-mechanics etc [10-17]. Progress in each of these areas depends upon the ability to selectivity and controllability deposit thin film thickness ranging from tens of angstroms to micro meter with specified physical properties. This, in turn, requires control often at the atomic level of film microstructure and microchemistry. There are a vast number of deposition method available and in use today [18-20]. However, all the methods have their specific limitation and involve compromises with respect to process specifications, substrate material limitations, expected film properties and cost. This makes it difficult to select the best technique for any specific application. The most important factor in preparation of thin film material is to control porosity and pore size for sensing low to high level moisture. Sol gel thin film moisture sensor has not yet come to commercial market. The objective of the goal is to develop low cost technology in this

area. The aims of these observations are at developing sensors by sol gel process [21-24] avoiding costly conventional process such as evaporation, chemical vapour deposition and sputtering where yield losses are very high and the cost is significant and expensive. The advantage of sol-gel process is low cost. Composition and micro structure of the material can be controlled.

2. Experimental

2.1. Preparation of the Thin Film

A porous thin film of γ -Al₂O₃ was prepared from 20 gm of Al-Sec.-Butoxide (C₁₂H₂₇Al₂O₃) dissolving in 150 cc hot water and keeping the solution at 90°C under stirring for 30 minutes. Peptization was done by 0.7 cc concentrated HNO₃ and refluxing overnight. After preparing the sol solution calculated amount of binder was added to the sol solution. Dip coating was done to the above solution on the gold plate. The green thin film was dried 4-5 hours. After drying the coated gel was cured at 450°C for 2 hour. For higher film thickness the dipping and drying process was repeated a number of times. The sintering was done only after the final dipping.

2.2. Methods of Characterization

The powder XRD patterns were measured by X-ray diffraction instrument (Philips PW 1730) using Cu K_α radiation. The morphology of the film was characterized by Field Effect Scanning Electron Micrograph (FESEM) and Atomic Force Micrograph (AFM). The characteristic curves of humidity sensitivity were carried out with LCR meter (model no. HP4284A) at room temperature. The controlled humidity environments were achieved using gas cylinders with different trace moisture level at ambient temperature which, yields from -64°C to -46°C DP respectively. The thin films were developed on a gold plate which was itself one of the electrodes and second electrode was screen printed (Model no-65 DEK, UK) on the surface of thin film. The figure of the sample is shown in Fig. 1.

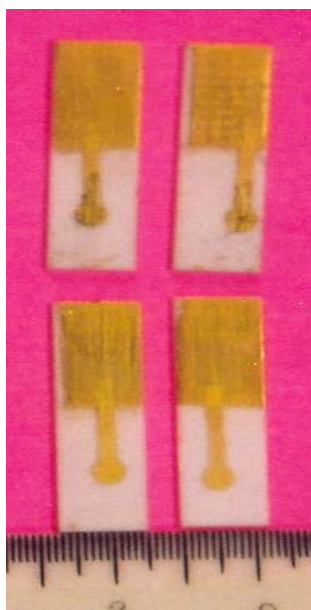


Fig. 1. Thin film sensor.

3. Results and Discussion

3.1. Film Thickness

Fig. 2 and Fig. 3 are the film thickness of sol-gel coat films. From the figures, we see that six coat film is much thicker than that of three coat. Higher the coating thickness lower is the sensitivity to moisture. Three coat is the optimum coating thickness to produce sensor materials. Below this thickness short circuit takes place and the materials can not be used as a sensor.

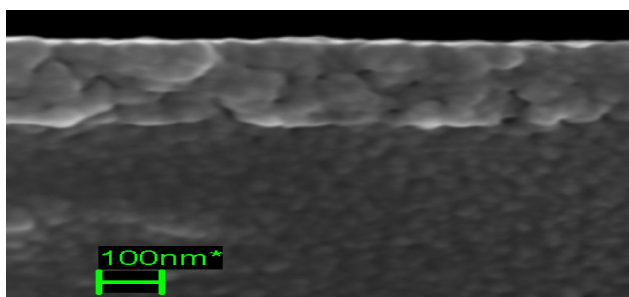


Fig. 2. Film thickness by six times dip coating measured by FESEM.

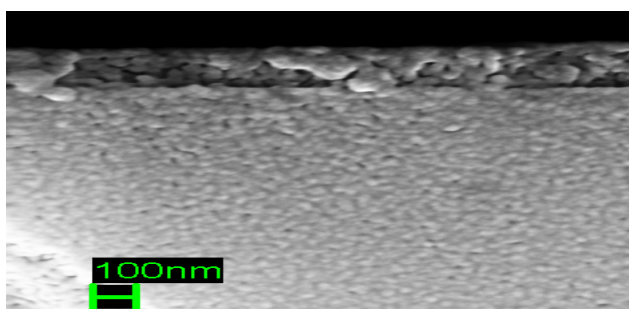


Fig. 3. Film thickness by three times dip coating measured by FESEM.

3.2. X-ray Diffraction

Fig. 4 is the crystalline phase of γ -Al₂O₃ powder, which is prepared from alumina sol on drying, then converted to gel and finally fired at 450⁰C in 1.5 hours. From the figure we see width of peak and peak height value is the identical to literature value. γ -phase alumina is highly sensitive to parts per million (PPM) moisture.

3.3. Surface Characterization by AFM

FESEM images of the coating sample are represented in Fig. 5 and Fig. 6. From the figure we see that the surfaces of the both samples are of nano porous dimensions. Topographic view of the surface of the three coat is represented in Fig. 3 and six coat in Fig. 6. The surface is rather smooth in Fig. 3 as compared to Fig. 6. The surface layer is composed of nanopore and gamma alumina grain.

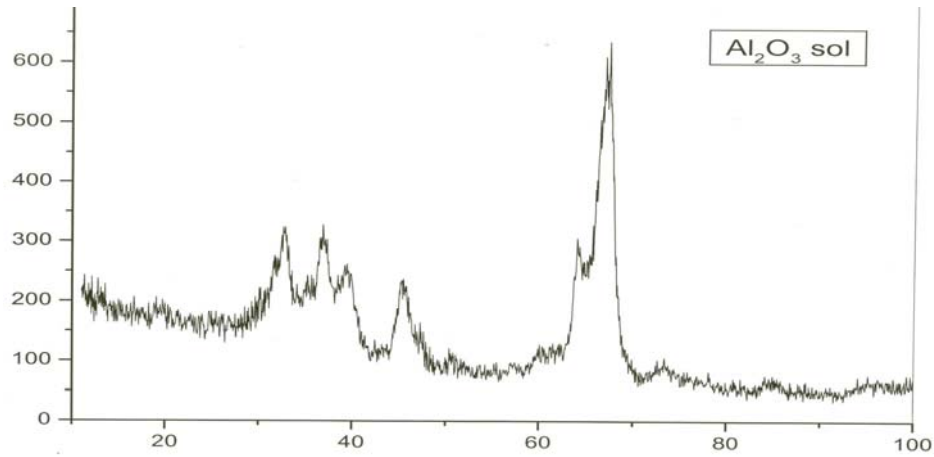


Fig. 4. γ -Al₂O₃ crystalline phase of coating sample.

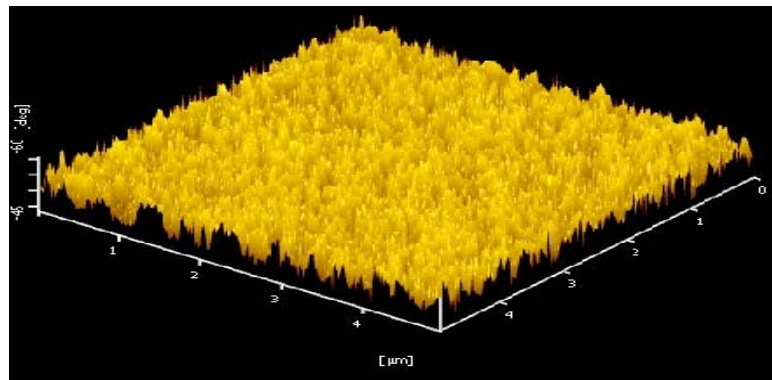


Fig. 5. 3D Structure of thin film with three times dip coating.

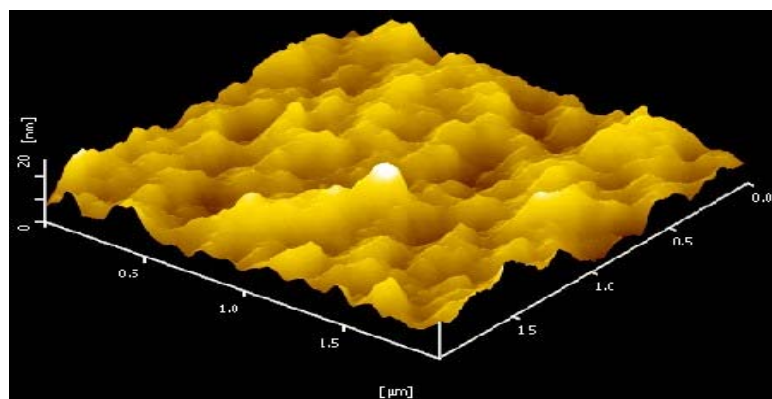


Fig. 6. 3D Structure of thin film with six times dip coating.

3.4. Surface Characterization by FESEM

Surface morphologies of thin film with six time dip coating and three time dip coating are shown in Fig. 7 and Fig.8 respectively.

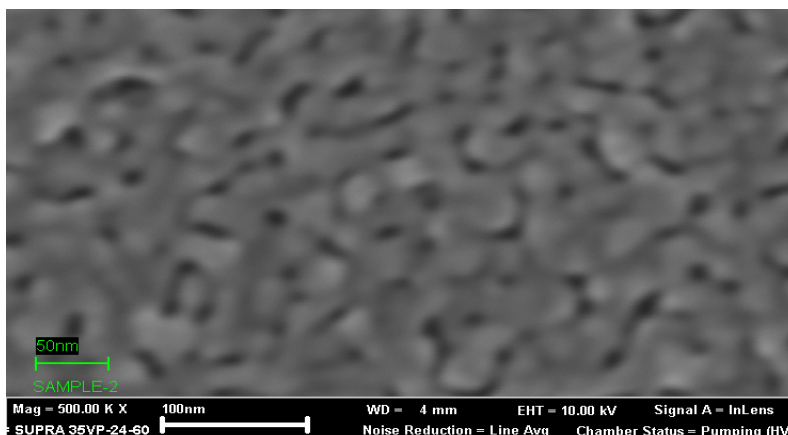


Fig. 7. Surface morphology of thin film with six time dip coating.

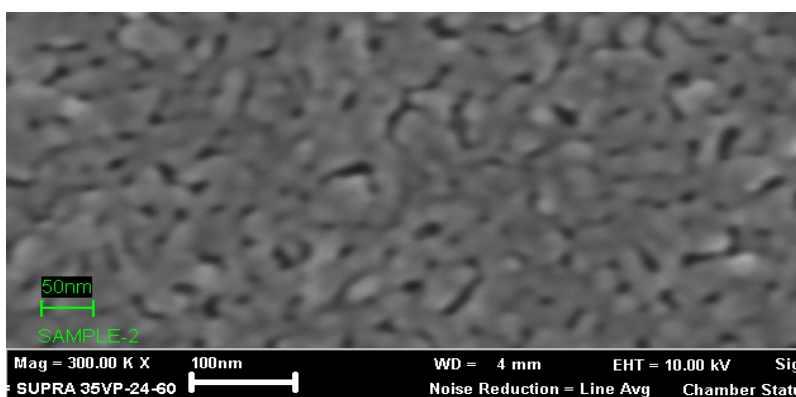


Fig. 8. Surface morphology of thin film with three time dip coating.

3.5. Trace Moisture Sensitive Property

The results of capacitance measurements as a function of trace moisture at room temperature are shown in Fig. 11. It can be seen that the change in capacitance at three coat is higher at a range up to -48°C DP showing higher humidity, sensitivity and resolution property. After six times coating the capacitance and resolution greatly decreased by five times due to higher thickness with the increase of moisture up to -48°C DP. The three coat exhibiting the maximum humidity sensitive property and linearity was selected for evaluation of hysteresis and response-recovery time.

Capacity on moisture and frequency depend on the three coat sample. It is seen that when the frequency is 100 Hz the capacity increases greatly with increasing moisture. However, when the higher frequency was used, such as 1 KHz, 10 KHz and 100 KHz the change in capacitance became less with increasing humidity.

The response and recovery time were shown in Fig. 9 and Fig. 10. The time taken by the sensor to achieve 90% of total capacitance change is defined as the response and recovery time. The response time of 3rd coated sample is 12 second (Fig. 10) shorter than the 6th coated sample shown in Fig. 9.

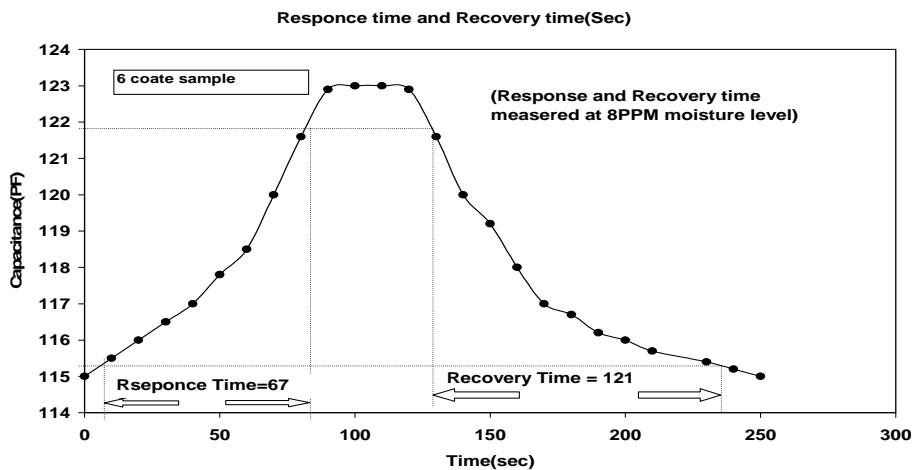


Fig. 9. Six time coating sample of Response and recovery time.

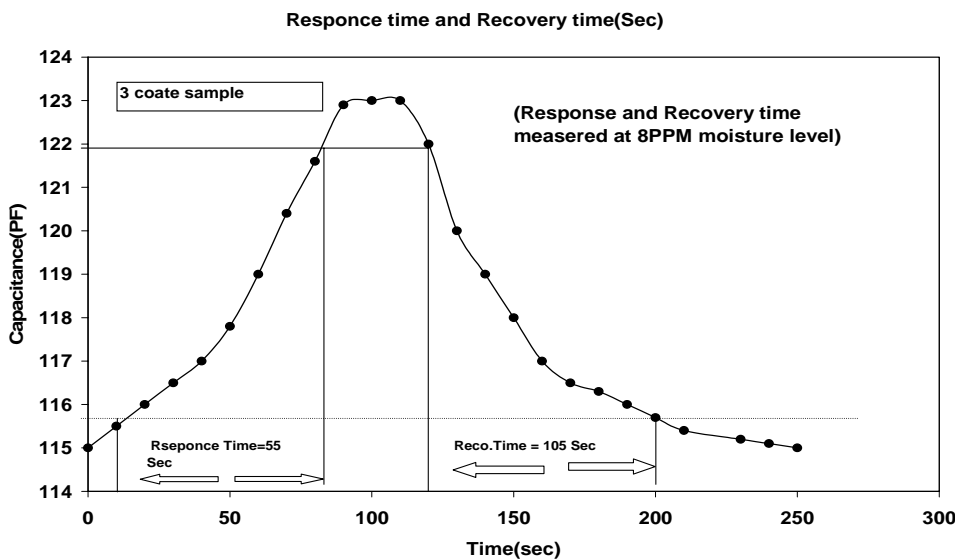


Fig. 10. Three time coating sample of Response and recovery time.

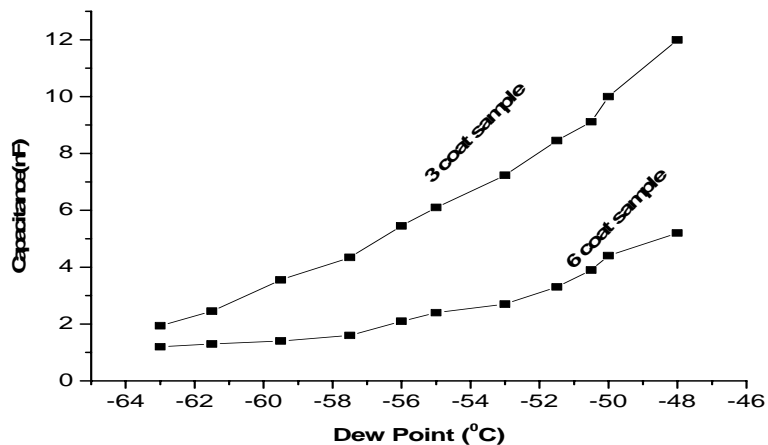


Fig. 11. Comparison between three coat and six coat sample.

Conclusion

Sol-gel thin film γ -Al₂O₃ was studied as humidity sensor material and their structure was characterized by XRD, FESEM and AFM. These tests indicate that the ordered nanoporous thin film coated structure is highly sensitive to trace moisture level.

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Guide for Contributors

Aims and Scope

Sensors & Transducers Journal (ISSN 1726- 5479) provides an advanced forum for the science and technology of physical, chemical sensors and biosensors. It publishes state-of-the-art reviews, regular research and application specific papers, short notes, letters to Editor and sensors related books reviews as well as academic, practical and commercial information of interest to its readership. Because it is an open access, peer review international journal, papers rapidly published in *Sensors & Transducers Journal* will receive a very high publicity. The journal is published monthly as twelve issues per annual by International Frequency Association (IFSA). In addition, some special sponsored and conference issues published annually.

Topics Covered

Contributions are invited on all aspects of research, development and application of the science and technology of sensors, transducers and sensor instrumentations. Topics include, but are not restricted to:

- Physical, chemical and biosensors;
- Digital, frequency, period, duty-cycle, time interval, PWM, pulse number output sensors and transducers;
- Theory, principles, effects, design, standardization and modeling;
- Smart sensors and systems;
- Sensor instrumentation;
- Virtual instruments;
- Sensors interfaces, buses and networks;
- Signal processing;
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- Nanosensors;
- Microsystems;
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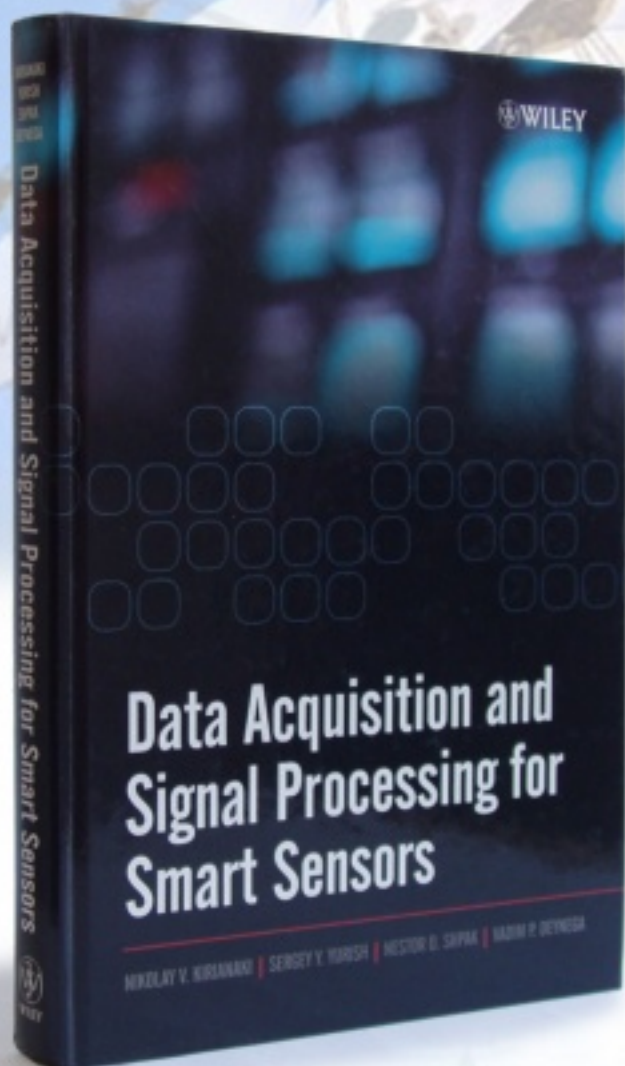
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